

**IN THE SPECIFICATION:**

1. Kindly replace the title of the invention on the cover page, page 1 and page 33 with the following:

**SiC MOSFET FOR USE AS A POWER SWITCH AND  
A METHOD OF MANUFACTURING THE SAME**

2. Kindly replace the paragraph beginning at page 5, line 13 with the following rewritten paragraph:

A<sup>1</sup> -- In another embodiment, the MOSFET further includes a buried oxide layer that may be formed in the substrate. The gate and substrate may be comprised of conventional materials, such as poly-silicon and silicon, respectfully. In those embodiments where the silicon carbide is formed on a silicon substrate, a 3C silicon carbide structure is formed. In yet another embodiment, the MOSFET is formed on a semiconductor wafer that includes a CMOS device, which, in certain embodiments, may form a drive controller for a power converter.--

3. Kindly replace the paragraph beginning at page 6, line 13, with the following rewritten paragraph:

A<sup>2</sup> --As was the case with the device, the method may also comprise forming a buried oxide layer in the substrate. Moreover, forming source and drain regions may comprise implanting an N-type dopant into the silicon carbide layer, which may be doped with a P-type dopant.--